

NextPower 100 V, 18 mΩ N-channel MOSFET in I2PAK package

10 April 2017

Product data sheet

1. General description

NextPower 100 V standard level gate drive MOSFET. Qualified to 175 °C and recommended for industrial & consumer applications.

2. Features and benefits

- · Optimised for fast switching, low spiking, high efficiency
- Low Q_G x R_{DSon} FOM for high efficiency switching applications
- Low body diode losses (Q_{rr}) and fast recovery (t_{rr})
- Strong avalanche energy rating (E_{AS})
- Avalanche rated & 100% tested
- Ha-free & RoHS compliant I2PAK low-height package

3. Applications

- Synchronous rectification in AC-to-DC and DC-to-DC applications
- Brushed & BLDC motor control
- UPS & solar inverter
- LED lighting
- Battery protection
- Full-bridge & half-bridge applications
- Flyback & resonant topologies

4. Quick reference data

Table 1. Qui	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	53	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	111	W
Tj	junction temperature			-55	-	175	°C
Static chara	acteristics					_	
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; Fig. 10		-	15	18	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; Fig. 11		-	22	28	mΩ
Dynamic ch	naracteristics	'					
Q _{GD}	gate-drain charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V;		-	4.2	-	nC
Q _{G(tot)}	total gate charge	Fig. 12; Fig. 13		-	21.4	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Avalanche ruggedness							
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$\begin{array}{l} {\sf I}_{\sf D} = 20.5 \; {\sf A}; \; {\sf V}_{sup} \le \; 100 \; {\sf V}; \; {\sf R}_{\sf GS} = 50 \; \Omega; \\ {\sf V}_{\sf GS} = 10 \; {\sf V}; \; {\sf T}_{j(init)} = 25 \; ^{\circ}{\rm C}; \; \underline{{\sf Fig. 4}}; \\ {\sf Unclamped} \end{array}$	[2]	-	-	109	mJ

[1] Avalanche current is limited by I_{AS}

[2] Protected by 100% test

5. Pinning information

Table 2. Pinning information					
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	G	gate	mb	D	
2	D	drain			
3	S	source		G-UFFA	
mb	D	mounting base; connected to drain		mbb076 S	
			I2PAK (SOT226)		

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
PSMN018-100ESF	I2PAK	plastic, single-ended package (I2PAK); 3 terminals; 2.54 mm pitch; 11 mm x 10 mm x 4.3 mm body	SOT226			

7. Marking

Table 4. Marking codes	
Type number	Marking code
PSMN018-100PSF	PSMN018-100PSF

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8. Limiting values

Table 5. Limiting values

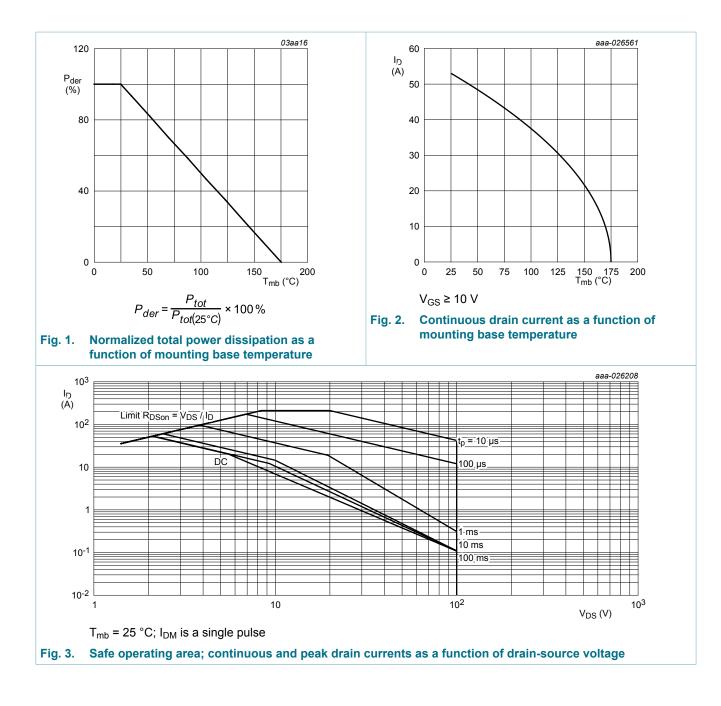
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	25 °C ≤ T _j ≤ 175 °C; R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage			-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	111	W
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	53	А
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	37	А
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$; Fig. 3		-	212	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode					
I _S	source current	T _{mb} = 25 °C		-	53	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	212	А
Avalanche r	uggedness		_			
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	$ \begin{array}{l} I_{D} = 20.5 \; \text{A}; \; V_{sup} \leq \; 100 \; \text{V}; \; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; \text{V}; \; \text{T}_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; \overline{\text{Fig. 4}}; \\ \text{Unclamped} \end{array} $	[2]	-	109	mJ
I _{AS}	non-repetitive avalanche current		[2]	-	20.5	A

[1] Avalanche current is limited by I_{AS}

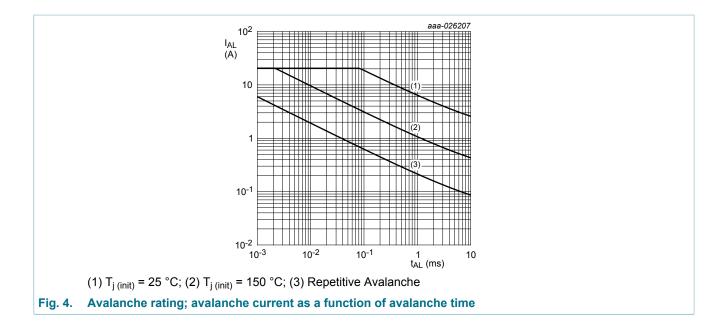
[2] Protected by 100% test

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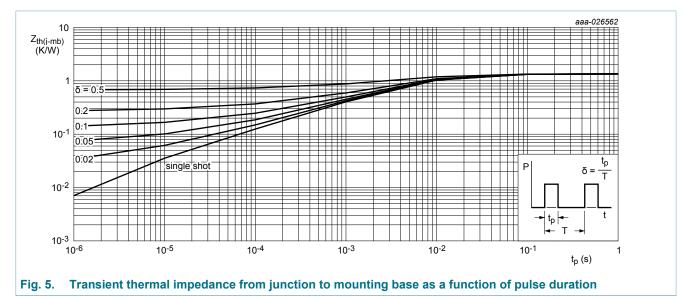
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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	1.22	1.35	K/W



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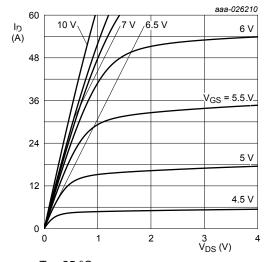
10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V _{(BR)DSS}	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C	100	-	-	V
. ,	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = -55 °C	-	3.6	-	V
	voltage	I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 175 °C	-	2.1	-	V
		I _D = 1 mA; V _{DS} =V _{GS} ; T _j = 25 °C; <u>Fig. 9</u>	2	3.2	4	V
$\Delta V_{GS(th)} / \Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 175 °C	-	-7.1	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	-	0.01	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 125 °C	-	-	100	μA
I _{GSS}	gate leakage current	V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	5	100	nA
		V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	5	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	15	18	mΩ
		V _{GS} = 7 V; I _D = 15 A; T _j = 25 °C; <u>Fig. 10</u>	-	17.9	27	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 100 °C; <u>Fig. 11</u>	-	22	28	mΩ
		V _{GS} = 10 V; I _D = 15 A; T _j = 175 °C; <u>Fig. 11</u>	-	31	40	mΩ
R _G	gate resistance	f = 1 MHz	-	1.58	-	Ω
Dynamic cha	aracteristics		·			
Q _{G(tot)}	total gate charge	I _D = 15 A; V _{DS} = 50 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	21.4	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	10.9	-	nC
Q _{GS}	gate-source charge	I_D = 15 A; V_{DS} = 50 V; V_{GS} = 10 V;	-	7.2	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	4.3	-	nC
Q _{GS(th-pl)}	post-threshold gate- source charge		-	2.9	-	nC
Q _{GD}	gate-drain charge		-	4.2	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 15 A; V _{DS} = 50 V; <u>Fig. 12; Fig. 13</u>	-	4.9	-	V
C _{iss}	input capacitance	V _{DS} = 50 V; V _{GS} = 0 V; f = 1 MHz;	-	1482	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>	-	280	-	pF
C _{rss}	reverse transfer capacitance		-	13	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; \text{ R}_{L} = 3.3 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	10.2	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C$	-	14.1	-	ns

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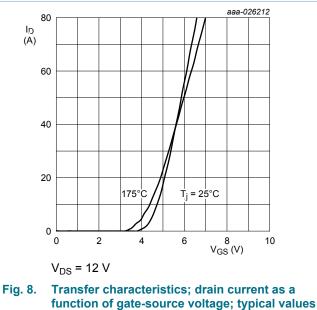
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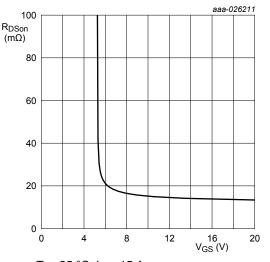
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
t _{d(off)}	turn-off delay time			-	17.3	-	ns
t _f	fall time			-	12.6	-	ns
Source-drain	Source-drain diode						
V _{SD}	source-drain voltage	I_{S} = 15 A; V_{GS} = 0 V; T_{j} = 25 °C; <u>Fig. 15</u>		-	0.9	1.2	V
t _{rr}	reverse recovery time	I_{S} = 15 A; dI _S /dt = -100 A/µs; V _{GS} = 0 V;		-	40	-	ns
Qr	recovered charge	V _{DS} = 50 V; <u>Fig. 16</u>		-	46	-	nC

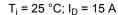














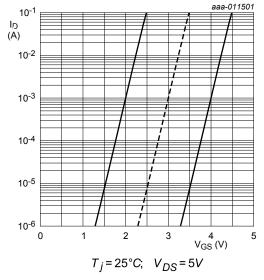
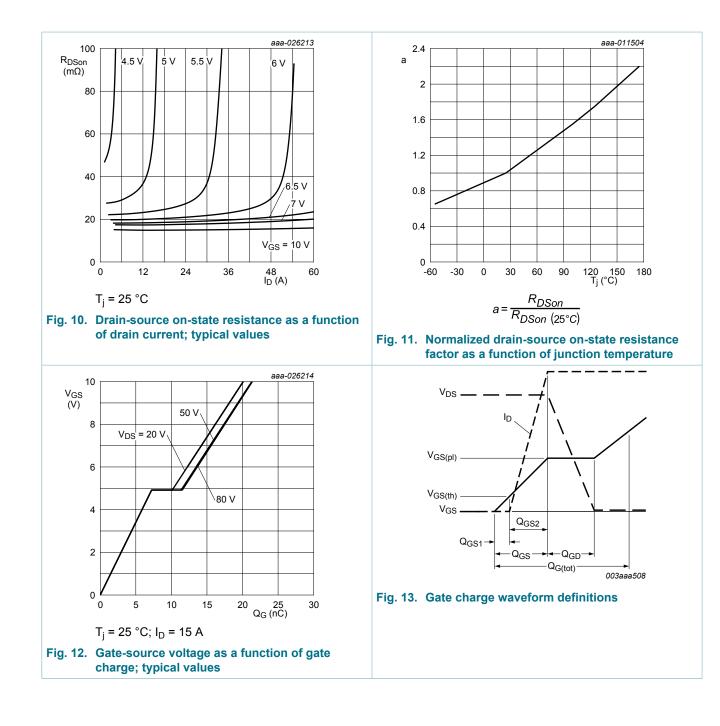


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

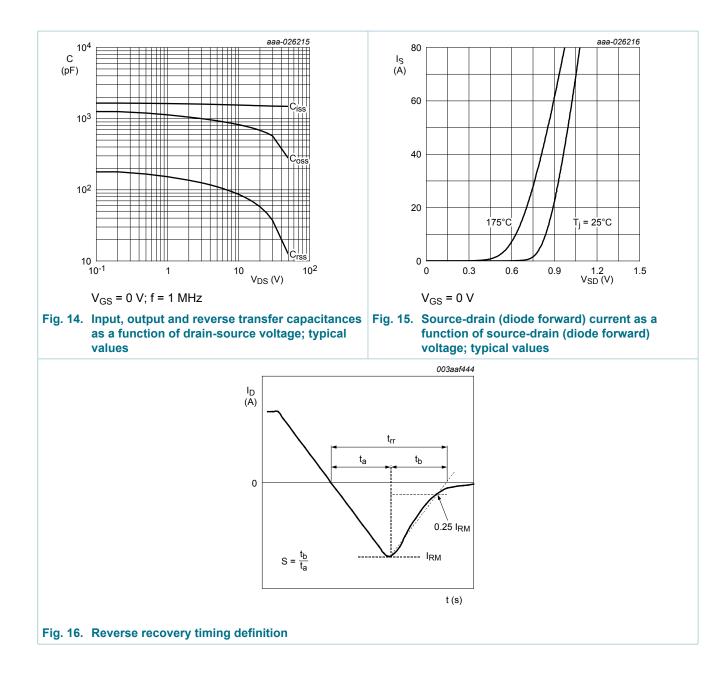
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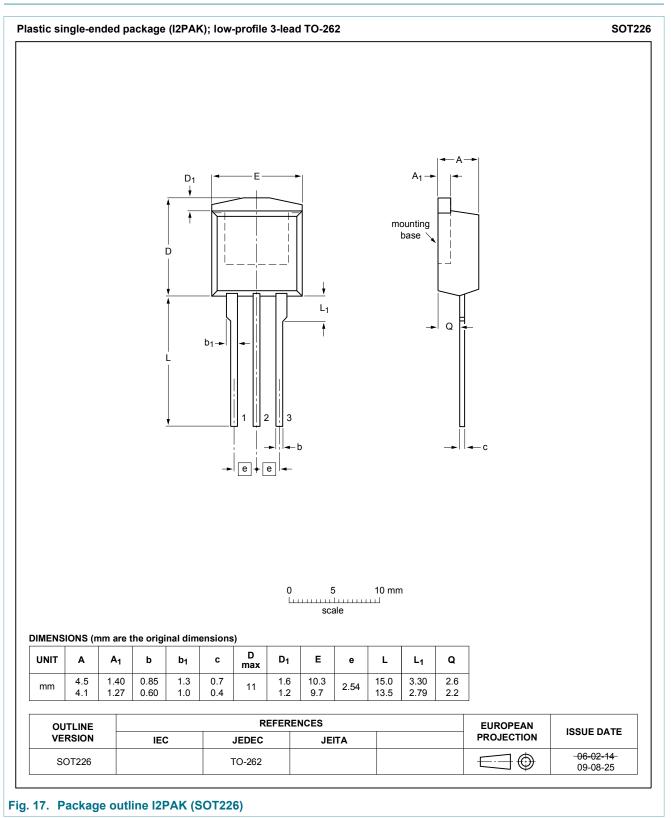


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11. Package outline



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12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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